## **AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in this application:

 (Previously Presented) A method for cleaning semiconductor wafers comprising:

dipping semiconductor wafers in a cleaning solution tank to which a cleaning solution is fed;

feeding ultrasonic waves into the cleaning solution after the passage of a prescribed period of time since the time that the semiconductor wafers are dipped in the cleaning solution;

wherein the prescribed period of time is 20 sec or more.

## 2. (Cancelled)

- 3. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 1 wherein the prescribed time corresponds to a substitution ratio of the cleaning solution in the cleaning solution tank of 0.4 or more.
- 4. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 1 wherein a time for the feeding ultrasonic waves into the cleaning solution is 400 sec or more.
- 5. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 4 wherein a total cleaning time for the semiconductor wafers is 600 sec or more.

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- 6. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 1 wherein the cleaning solution is ultra-pure water.
- 7. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 1 wherein the cleaning solution is hydrogen-enriched ultra-pure water.
- 8. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 7 wherein a concentration of hydrogen in the hydrogen-enriched ultra-pure water is in the range of 0.3-1.6 ppm.
- 9. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 1 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.
  - 10. (Canceled)
  - 11. (Canceled)
- 12. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 3 wherein the cleaning solution is hydrogen-enriched ultra-pure water.
- 13. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 4 wherein the cleaning solution is hydrogen-enriched ultra-pure water.

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14. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 5 wherein the cleaning solution is hydrogen-enriched ultra-pure water.

## 15. (Canceled)

- 16. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 3 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.
- 17. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 4 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.
- 18. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 5 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.
- 19. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 6 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.

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20. (Previously Presented) The method for cleaning semiconductor wafers described in Claim 7 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.

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## **AMENDMENTS TO THE DRAWINGS:**

The attached formal drawing set adds FIG. 4 (former "Table 1"), FIG. 5 (former "Table 2"), and FIG. 6 (former "Table 3"). Sheets 1-3 submitted herewith replace the original drawing sheets.

Attachment: Replacement Sheets (3)

Annotated Sheets Showing Changes (2)

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